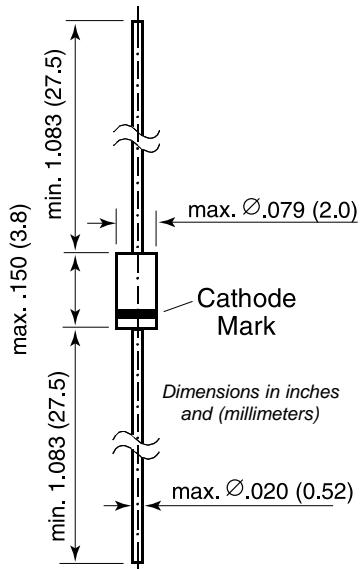

**DO-204AH (DO-35 Glass)**


## Small Signal Diode

Reverse Voltage 100V  
Forward Current 150mA

### Features

- Silicon Epitaxial Planar Diode
- Fast switching diode

### Mechanical Data

**Case:** DO-35 Glass Case

**Weight:** approx. 0.13g

#### Packaging Codes/Options:

D7/10K per 13" reel (52mm tape), 20K/box  
D8/10K per Ammo tape (52mm), 20K/box  
F2/10K per Ammo tape (52mm), 50K/box  
F3/10K per 13" reel (52mm tape), 50K/box

### Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Reverse voltage	VR	75	V
Peak reverse voltage	V <sub>RM</sub>	100	V
Maximum average rectified current half wave rectification with resistive load at T <sub>amb</sub> = 25°C and f ≥ 50Hz	I <sub>F(AV)</sub>	150 <sup>(1)</sup>	mA
Surge forward current at t < 1s and T <sub>j</sub> = 25°C	I <sub>FSM</sub>	500	mA
Maximum power dissipation at T <sub>amb</sub> = 25°C	P <sub>tot</sub>	500 <sup>(1)</sup>	mW
Maximum junction temperature	T <sub>J</sub>	175	°C
Storage temperature range	T <sub>S</sub>	-65 to +175	°C

### Electrical Characteristics (TA = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Max.	Unit
Maximum forward voltage drop at I <sub>F</sub> = 10mA	V <sub>F</sub>	-	1.0	V
Leakage current at V <sub>R</sub> = 50V at V <sub>R</sub> = 75V	I <sub>R</sub>	-	100 5	nA μA
Reverse breakdown voltage tested with 100μA pulses	V <sub>(BR)R</sub>	100	-	V
Capacitance at V <sub>F</sub> = V <sub>R</sub> = 0V	C <sub>tot</sub>	-	2	pF
Reverse recovery time from I <sub>F</sub> = 10mA to I <sub>R</sub> = 1mA, V <sub>R</sub> = 6V, R <sub>L</sub> = 100Ω	t <sub>rr</sub>	-	4	ns
Thermal resistance junction to ambient air	R <sub>θJA</sub>	-	350 <sup>(1)</sup>	°C/W
Rectification efficiency at f = 100MHz, V <sub>RF</sub> = 2V	η <sub>V</sub>	0.45	-	-

**Note:**

(1) Valid provided that leads at a distance of 8mm from case are kept at ambient temperature

## Small Signal Diode

### Ratings and Characteristic Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

